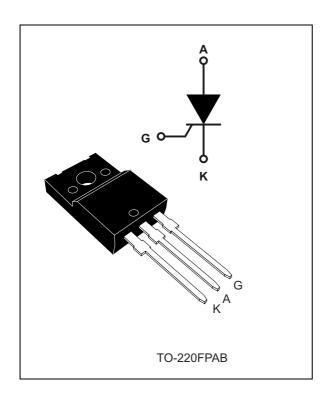
TN1605H-6FP



High temperature 16 A SCRs

Datasheet - production data



Features

- High junction temperature: T_i = 150 °C
- High noise immunity dV/dt = 200 V/μs up to 150 °C
- Gate triggering current I_{GT} = 6 mA
- Blocking voltage V_{DRM}/V_{RRM} = 600 V
- High turn on current rise dl/dt: 100 A/µs
- ECOPACK[®]2 compliant component
- Complies with UL standards (File ref: E81734)
- Insulated package TO-220FPAB:
 - Insulated voltage: 2000 VRMS

Applications

- · Voltage regulator circuits for motorbikes
- · Inrush current limiting circuits
- Motor control circuits and starters
- Light dimmers
- Solid state relays

Description

Thanks to a junction temperature up to 150 °C and an insulated TO-220FPAB package, the TN1605H-6FP offers high thermal performance up to 16 A rms.

The trade-off between the device's noise immunity (dV/dt = 200 V/ μ s), its gate triggering current (I_{GT} = 6 mA) and its turn-on current rise (dI/dt = 100 A/ μ s) allows the design of robust and compact control circuits for voltage regulators in motorbikes and industrial drives, overvoltage crowbar protection, motor control circuits in power tools and kitchen appliances, and inrush current limiting circuits.

The insulated fullpack package allows a back-to-back configuration.

Table 1. Device summary

Order code	Package	V _{DRM} /V _{RRM}	I _{GT}
TN1605H-6FP	TO-220FPAB	600 V	6 mA

Characteristics TN1605H-6FP

1 Characteristics

Table 2. Absolute ratings

Symbol	Parameter	Value	Unit		
I _{T(RMS)}	On-state rms current (180° conduction angle)		T _c = 83 °C	16	Α
			T _C = 83 °C	10	
I _{T(AV)}	Average on-state current (180° conduction angle)		T _C = 102 °C	8	А
			T _C = 117 °C	6	
ı	Non repetitive surge peak on-state current $(T_j \text{ initial} = 25 \text{ °C})$		t = 8.3ms	153	
I _{TSM}			t = 10 ms	140	A
l ² t	I ² t value for fusing (T _j initial = 25 °C)		t _p = 10 ms	98	A ² s
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}, t_r \le 100 \text{ ns}, T_i = 25 \text{ °C}$		f = 60 Hz	100	A/µs
V _{DRM} , V _{RRM}	Repetitive peak off-state voltage		600	V	
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 150 °C	4	Α
P _{G(AV)}	Average gate power dissipation		T _j = 150 °C	1	W
T _{stg}	Storage junction temperature range Operating junction temperature range		•	- 40 to + 150	°C
Tj				- 40 to + 150	
T_L	Maximum lead temperature for soldering during 10 s		260	°C	
V _{ins}	Insulation rms voltage, 1 minute TO-220FPAB			2000	V

Table 3. Electrical characteristics ($T_j = 25$ °C, unless otherwise specified)

Symbol	Test conditions			Value	Unit
			Min.	3.5	
I_{GT}	$V_D = 12 \text{ V}, R_L = 33 \Omega$		Тур.	4.5	mA
			Max.	6	Ì
V _{GT}	$V_D = 12 \text{ V}, R_L = 33 \Omega$		Max.	1.3	V
$V_{\sf GD}$	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega$ $T_j = 150 ^{\circ}\text{C}$		Min.	0.2	V
I _H	I _T = 500 mA, gate open		Max.	20	mA
IL	I _G = 1.2 x I _{GT}		Max.	40	mA
dV/dt	V _D = 402 V, gate open	T _j = 150 °C	Min.	200	V/µs
t _{gt}	$I_T = 32 \text{ A}, V_D = 600 \text{ V}, I_G = 100 \text{ mA},$ $(dI_G/dt)max = 0.2 \text{ A/µs}$		Тур	1.9	μs
t _q	$V_D = 402 \text{ V}, V_R = 25 \text{ V}, I_T = 16 \text{ A}, \\ (dI_G/dt) max = 30 \text{A}/\mu \text{s}, dV_D/dt = 40 \text{ V}/\mu \text{s} $ $T_j = 150 \text{ °C}$		Тур	70	μs

TN1605H-6FP Characteristics

Table 4. Static characteristics

Symbol	Test conditions		Value	Unit	
V_{TM}	$I_{TM} = 32 \text{ A}, t_p = 380 \ \mu \text{s}$	T _j = 25 °C	Max.	1.6	V
V _{t0}	Threshold voltage	T _j = 150 °C	Max.	0.82	V
R _d	Dynamic resistance	T _j = 150 °C	Max.	25	mΩ
I _{DRM,}	$V_D = V_{DRM}, V_R = V_{RRM}$	T _j = 25 °C	Max.	5	μΑ
I _{RRM}		T _j = 150 °C	iviax.	1.5	mA

Table 5. Thermal resistance

S	Symbol	Parameter	Value	Unit
F	R _{th(j-c)}	Junction to case (AC)	4.5	°C/W
F	R _{th(j-a)}	Junction to ambient (DC)	60	°C/W

Figure 1. Maximum power dissipation versus average on-state current

P(W) 18 16 α = 180 ° DC 14 α = 120 ° $\alpha = 90$ 12 10 8 6 4 2 $I_{T(AV)}(A)$ 5 10 15

Figure 2. Average and DC on-state current versus case temperature

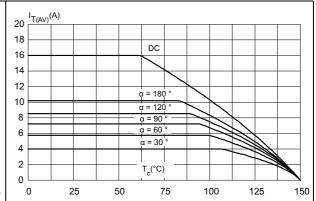
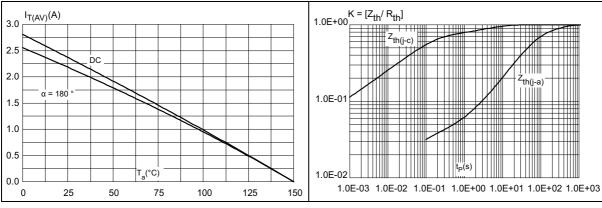


Figure 3. Average and DC on-state current versus ambient temperature

Figure 4. Relative variation of thermal impedance versus pulse duration



Characteristics TN1605H-6FP

Figure 5. Relative variation of gate triggering current and gate voltage versus junction temperature (typical values)

2.5 2.0 1.5 1.0 V_{GT} 0.5 0.0 -50 -25 0 25 50 75 100 125 150

Figure 6. Relative variation of holding current and latching current versus junction temperature (typical values)

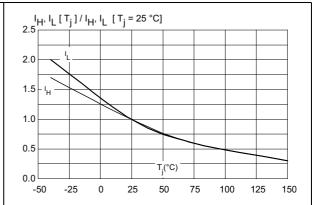
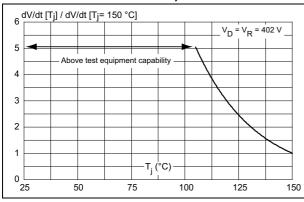


Figure 7. Relative variation of static dV/dt immunity versus junction temperature (typical values)

Figure 8. Surge peak on-state current versus number of cycles



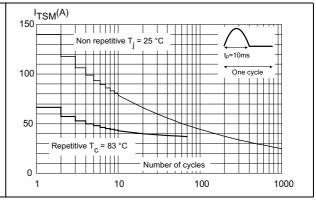


Figure 9. Non-repetitive surge peak on-state current for a sinusoidal pulse (tp < 10 ms)

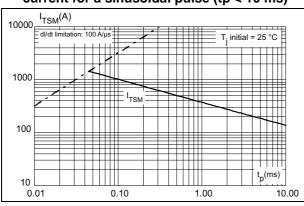
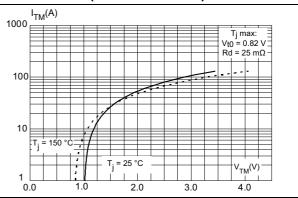
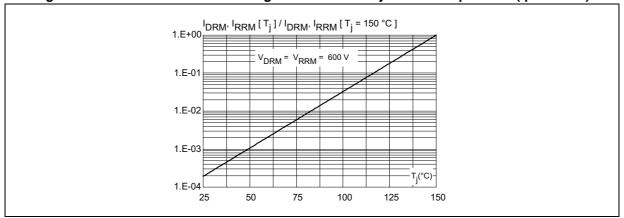


Figure 10. On-state characteristics (maximum values)



TN1605H-6FP Characteristics

Figure 11. Relative variation of leakage current versus junction temperature (tp < 10 ms)



Package information TN1605H-6FP

Package information 2

- Epoxy meets UL94, V0
- Lead-free package
- Halogen free molding compound
- Recommended torque: 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Н Dia L6 L2 L7 L3 L5 D F1 L4 F2 F G1 G

Figure 12. TO-220FPAB dimension definitions

Table 6. TO-220FPAB dimensions

	Dimensions				
Ref.	Millin	Millimeters		hes	
	Min.	Max.	Min.	Max.	
А	4.4	4.6	0.173	0.181	
В	2.5	2.7	0.098	0.106	
D	2.5	2.75	0.098	0.108	
Е	0.45	0.70	0.018	0.027	
F	0.75	1	0.030	0.039	
F1	1.15	1.70	0.045	0.067	
F2	1.15	1.70	0.045	0.067	
G	4.95	5.20	0.195	0.205	
G1	2.4	2.7	0.094	0.106	
Н	10	10.4	0.393	0.409	
L2	16 ⁻	Гур.	0.63	Тур.	
L3	28.6	30.6	1.126	1.205	
L4	9.8	10.6	0.386	0.417	
L5	2.9	3.6	0.114	0.142	
L6	15.9	16.4	0.626	0.646	
L7	9.00	9.30	0.354	0.366	
Dia.	3.00	3.20	0.118	0.126	

Ordering information TN1605H-6FP

3 Ordering information

Figure 13. Ordering information scheme

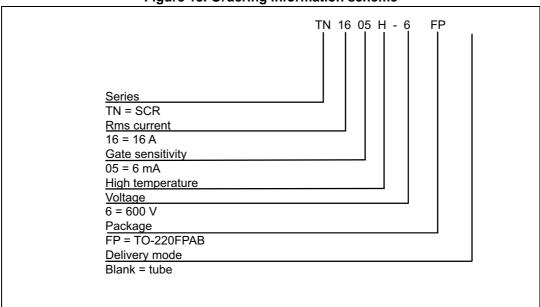


Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
TN1605H-6FP	TN1605H6	TO-220FPAB	2.0 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
24-Feb-2015	1	Initial release.

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